

Interpreting Inorganic Compositional Depth Profiles to Understand the Rate-Limiting Step in Vapor Phase Infiltration Processes

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Supporting Information

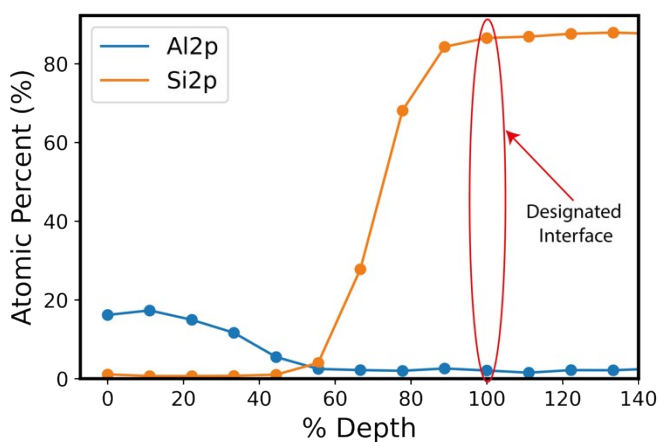


Figure S1: XPS depth profile used to determine infiltration depth of inorganic precursor. 100% depth is chosen as the point where the silicon signal plateaus.